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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Hirokazu SAYAMA, et al.

SERIAL NO: 10/620,379

FILED: July 17, 2003

FOR: SEMICONDUCTOR DEVICE INCLUDING GATE ELECTRODE FOR
APPLYING TENSILE STRESS TO SILICON SUBSTRATE, AND METHOD
OF MANUFACTURING THE SAME

GROUP: 2812

ATTENTION:
FILING RECEIPT CORRECTIONS

REQUEST FOR CORRECTED OFFICIAL FILING RECEIPT

Office of Initial Patent Examination
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:


The Patent Office is requested to provide a corrected Official Filing Receipt for the
attached. No fees are required. If you have any questions, please do not hesitate to contact us.

Respectfully Submitted,

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APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/620,379	07/17/2003	2812	750	240438US2	14	18	2

CONFIRMATION NO. 8754

FILING RECEIPT



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1940 DUKE STREET
ALEXANDRIA, VA 22314

Date Mailed: 10/21/2003

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections, facsimile number 703-746-9195. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

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DOCKETING DEPT.

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Assignment For Published Patent Application

Renesas Technology Corp., Tokyo, JAPAN;

Domestic Priority data as claimed by applicant

Foreign Applications

JAPAN 2002-336669 11/20/2002

If Required, Foreign Filing License Granted: 10/20/2003

Projected Publication Date: 05/20/2004

Non-Publication Request: No

Early Publication Request: No

Title

Semiconductor device including gate electrode for applying tensile stress to silicon substrate, and method of manufacturing the same

Priority Class

438

PLEASE NOTE THAT THE TITLE IS INCORRECT. IT SHOULD READ AS FOLLOWS:

SEMICONDUCTOR DEVICE INCLUDING GATE ELECTRODE FOR APPLYING
TENSILE STRESS TO SILICON SUBSTRATE, AND METHOD OF MANUFACTURING
THE SAME